

GATE DRIVE TRANSFORMERS 栅极驱动变压器

56P3362

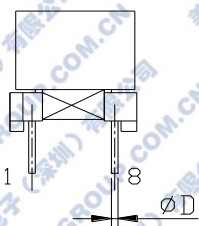
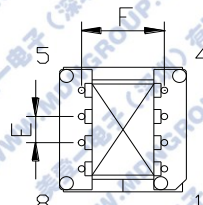
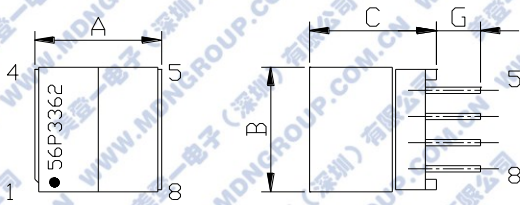
FEATURES

- Gate drive transformers are used to deliver the controlling gate-voltage pulses between the drain and source of a MOSFET, while providing isolation between the MOSFET and the controlling drive circuit. Gate-driver circuits need an isolated (floating) bias supply to maintain the required turn-on bias when the FET source rises to the input voltage. A gate drive transformer isolates the controlling gate-drive circuit from the switch node when driving the MOSFET gate and may also scale the output voltage via an appropriate primary-to-secondary turns ratio.

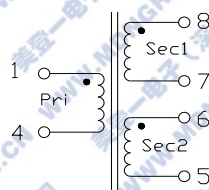
APPLICATIONS

- Designed for ON Semiconductor Power Factor Correction and Flyback Controllers.

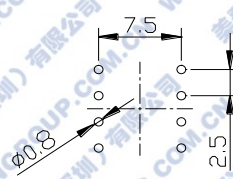
DIMENSIONS AND LAND PATTERNS(mm)



SCHEMATICS



LAND PATTERN



A max	B max	C max	D±0.1	E±0.2	F±0.2	G±0.2
12.0	13.0	12.0	0.60	2.50	7.50	4.0

SPECIFICATION

P/N	L (mH) ± 30%	Lk (uH) Max	DCR(Ω)		ET (V-μsec) Min	Turns ratio Pri:Sec	Hipot Pri-Sec	Hipot Sec-Sec
			Pri Max	Sec Max				
56P3362	1.30	0.35	0.35	0.80	45	1:1	3750V/2SEC	1500V/2SEC

Notes: L&Lk test frequency 100KHz/1.0V.

特 征

- 栅极驱动变压器用于在 MOSFET 的漏极和源极之间传递控制栅极电压脉冲，同时在 MOSFET 和控制驱动电路之间提供隔离。栅极驱动电路需要一个隔离（浮动）偏置电源，以在 FET 源上上升到输入电压时保持所需的导通偏置。栅极驱动变压器在驱动 MOSFET 栅极时将控制栅极驱动电路与开关节点隔离，并且还可以通过适当的一次到二次匝数比来缩放输出电压。

用 途

- 用于半导体功率因数校正和反激控制器的设计。